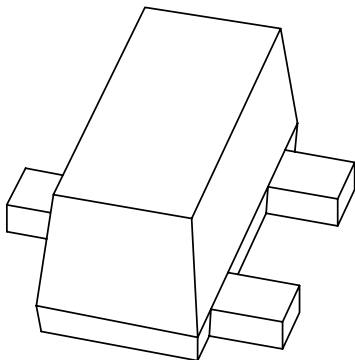


DATA SHEET



PBSS2515F

15 V low V_{CEsat} NPN transistor

Product specification
Supersedes data of 2001 Jan 26

2001 Sep 21

15 V low V_{CEsat} NPN transistor

PBSS2515F

FEATURES

- Low collector-emitter saturation voltage
- High current capabilities
- Improved thermal behaviour due to flat leads.

APPLICATIONS

- General purpose switching and muting
- Low frequency driver circuits
- LCD backlighting
- Audio frequency general purpose amplifier applications
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

NPN low V_{CEsat} transistor in a SC-89 (SOT490) plastic package.
 PNP complement: PBSS3515F.

MARKING

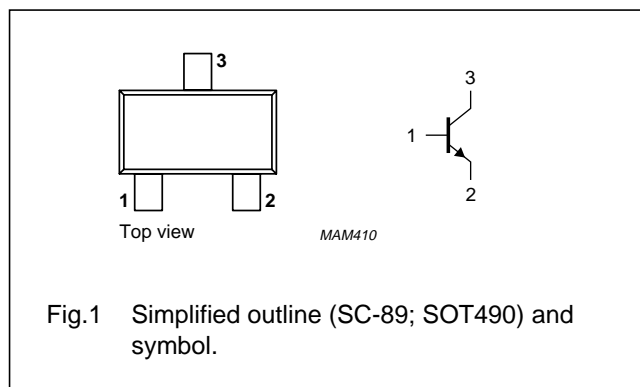
TYPE NUMBER	MARKING CODE
PBSS2515F	2A

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	15	V
I_C	collector current (DC)	500	mA
I_{CM}	peak collector current	1	A
R_{CEsat}	equivalent on-resistance	<500	m Ω

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	15	V
V_{CEO}	collector-emitter voltage	open base	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	6	V
I_C	collector current (DC)		–	500	mA
I_{CM}	peak collector current		–	1	A
I_{BM}	peak base current		–	100	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^\circ\text{C}$	–	250	mW
T_{stg}	storage temperature		–65	+150	$^\circ\text{C}$
T_j	junction temperature		–	150	$^\circ\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^\circ\text{C}$

15 V low V_{CEsat} NPN transistor

PBSS2515F

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-a}$	thermal resistance from junction to ambient	in free air	500	K/W

CHARACTERISTICS

$T_{amb} = 25\text{ °C}$; unless otherwise specified.

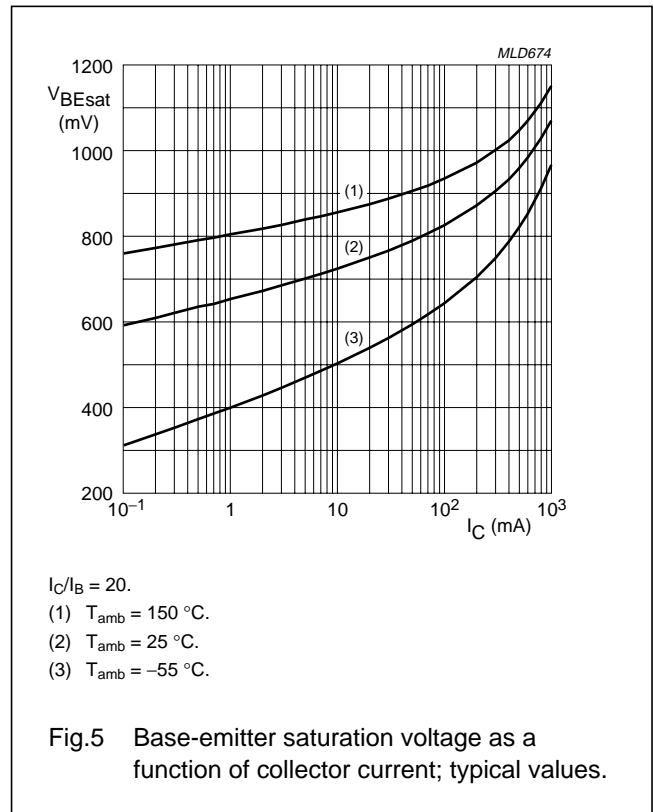
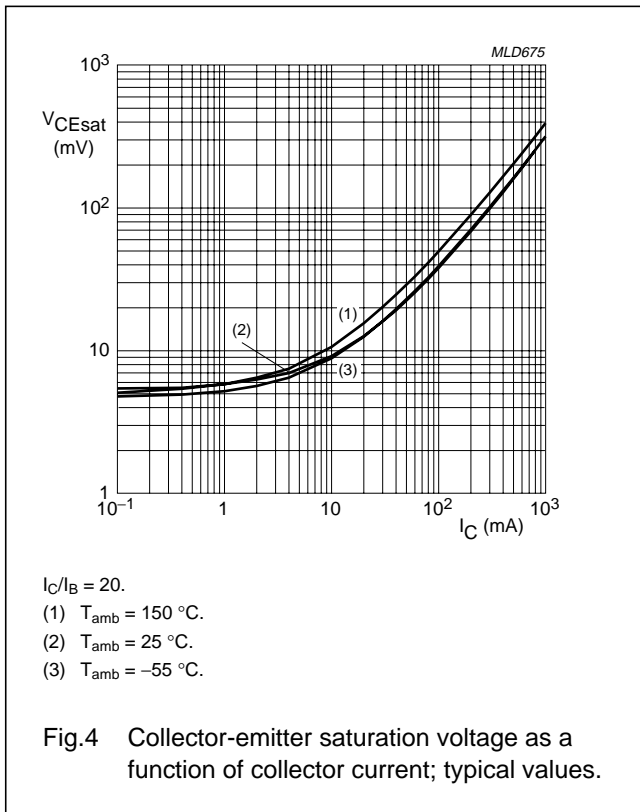
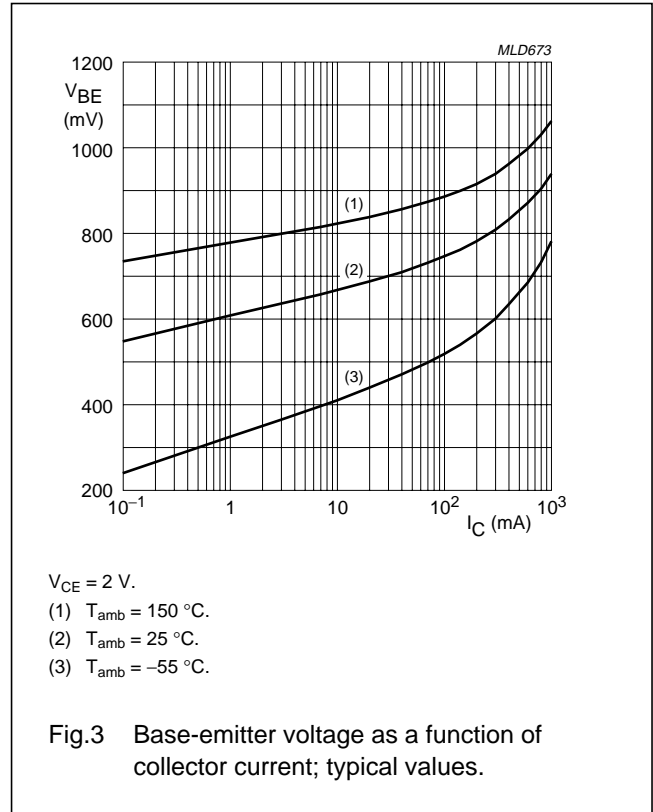
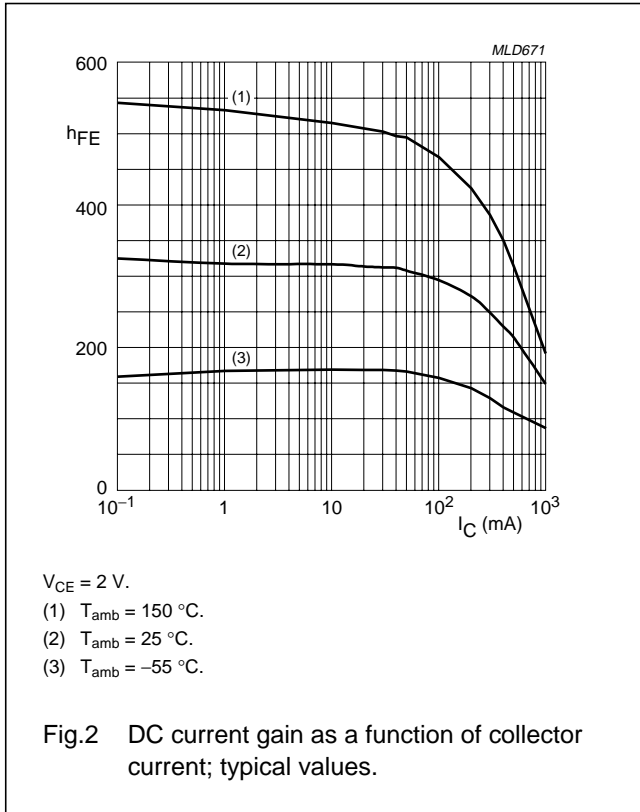
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = 15\text{ V}; I_E = 0$	–	–	100	nA
		$V_{CB} = 15\text{ V}; I_E = 0; T_J = 150\text{ °C}$	–	–	50	μA
I_{EBO}	emitter-base cut-off current	$V_{EB} = 5\text{ V}; I_C = 0$	–	–	100	nA
h_{FE}	DC current gain	$V_{CE} = 2\text{ V}; I_C = 10\text{ mA}$	200	–	–	
		$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}; \text{note 1}$	150	–	–	
		$V_{CE} = 2\text{ V}; I_C = 500\text{ mA}; \text{note 1}$	90	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = 10\text{ mA}; I_B = 0.5\text{ mA}$	–	–	25	mV
		$I_C = 200\text{ mA}; I_B = 10\text{ mA}$	–	–	150	mV
		$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	250	mV
R_{CEsat}	equivalent on-resistance	$I_C = 500\text{ mA}; I_B = 50\text{ mA}$	–	300	<500	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = 500\text{ mA}; I_B = 50\text{ mA}; \text{note 1}$	–	–	1.1	V
V_{BE}	base-emitter turn-on voltage	$V_{CE} = 2\text{ V}; I_C = 100\text{ mA}; \text{note 1}$	–	–	0.9	V
f_T	transition frequency	$I_C = 100\text{ mA}; V_{CE} = 5\text{ V};$ $f = 100\text{ MHz}$	250	420	–	MHz
C_c	collector capacitance	$V_{CB} = 10\text{ V}; I_E = I_e = 0; f = 1\text{ MHz}$	–	4.4	6	pF

Note

1. Pulse test: $t_p \leq 300\ \mu\text{s}$; $\delta \leq 0.02$.

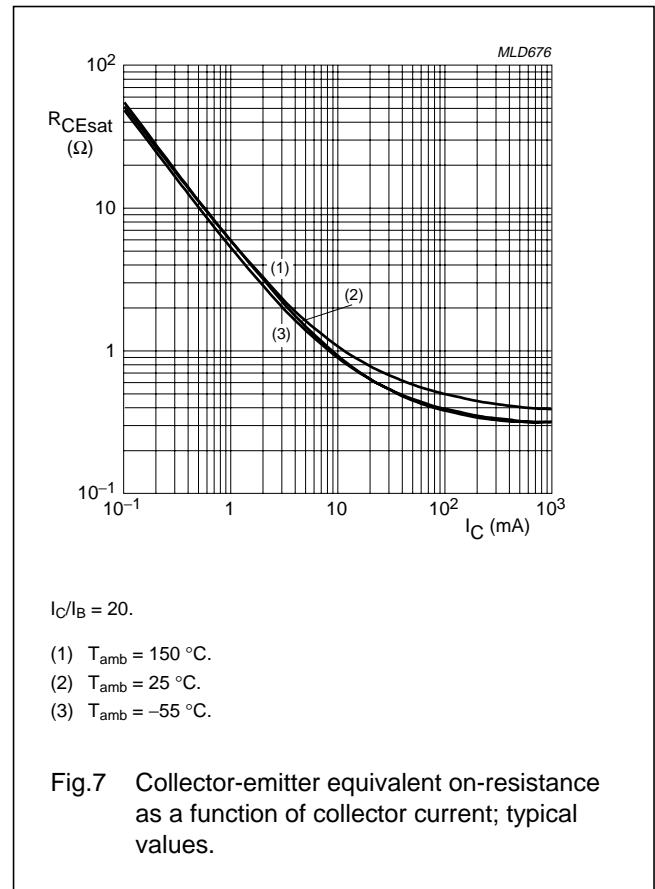
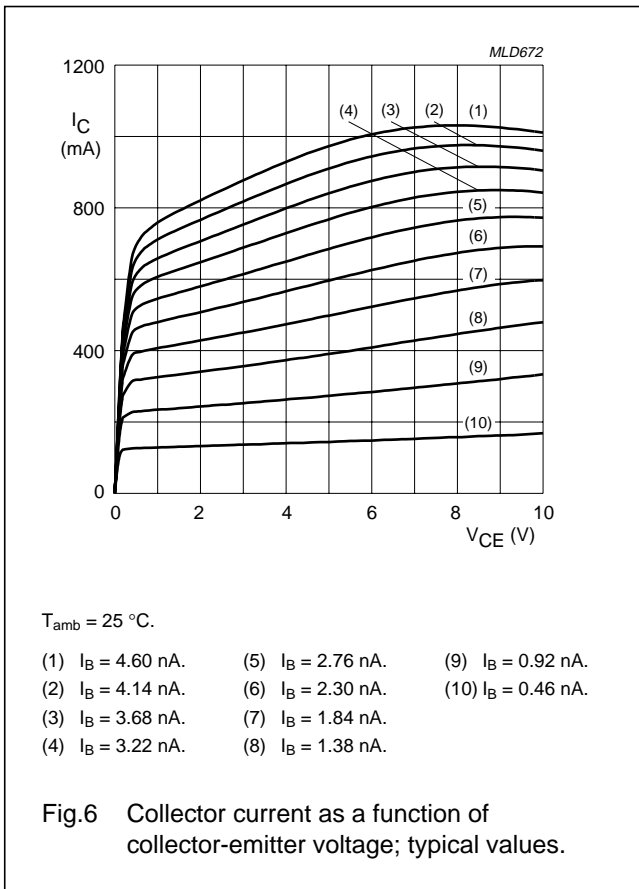
15 V low V_{CEsat} NPN transistor

PBSS2515F



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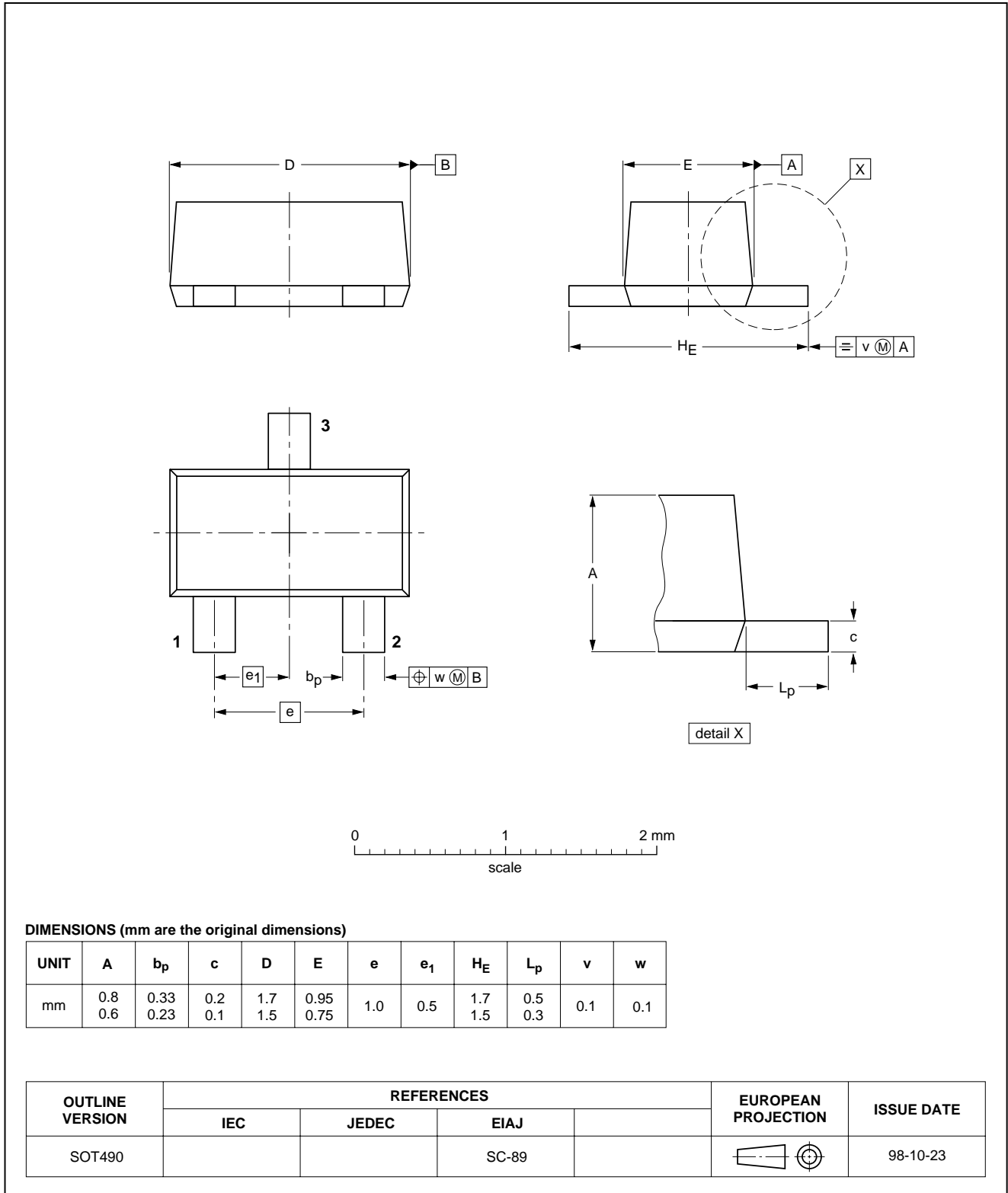
15 V low V_{CEsat} NPN transistor

PBSS2515F

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT490



15 V low V_{CEsat} NPN transistor

PBSS2515F

DATA SHEET STATUS

DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITIONS
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